

NTE2328 (NPN) & NTE2329 (PNP) Silicon Complementary Transistors Audio Power Output

Features:

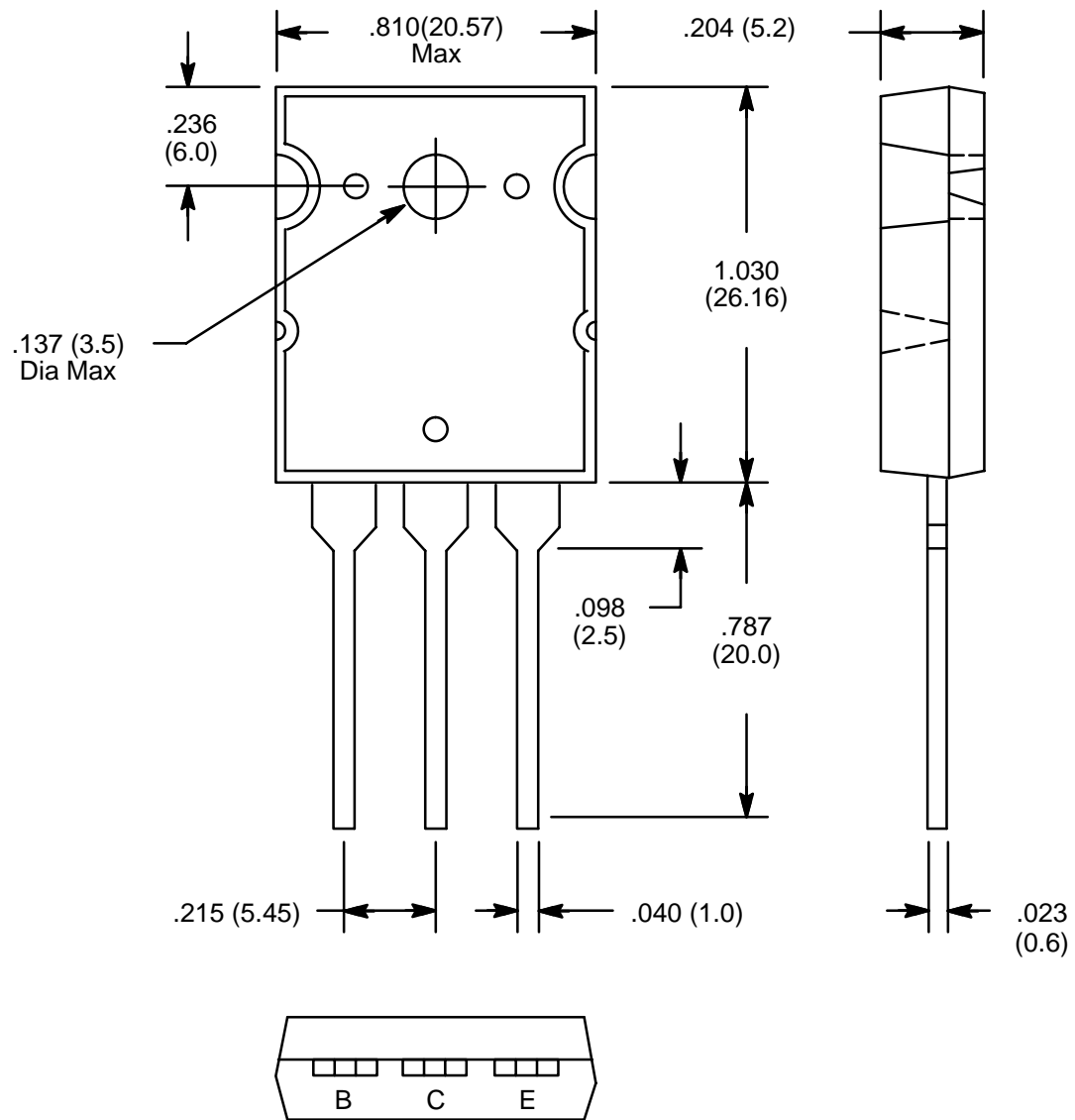
- Recommended for 100W High Fidelity Audio Frequency Amplifier Output Stage

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	200V
Collector–Emitter Voltage, V_{CEO}	200V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	15A
Base Current, I_B	1.5A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	150W
Operating Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 200\text{V}, I_E = 0$	–	–	5.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}, I_C = 0$	–	–	5.0	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50\text{mA}, I_B = 0$	200	–	–	V
DC Current Gain	h_{FE1}	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	55	–	160	
	h_{FE2}	$V_{CE} = 5\text{V}, I_C = 8\text{A}$	35	60	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{A}, I_B = 1\text{A}$	–	1.5	3.0	V
Base–Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 8\text{A}$	–	1.0	1.5	V
Transistion Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	–	25	–	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	–	470	–	pF



Note: Collector connected to heat sink.